

 Dual bidirectional I3C/I<sup>2</sup>C-bus and SPI voltage-level translator

 Rev. 1.0 — 10 May 2021

 Product data sheet

**1** General description

The P3A9606JK is a 2-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation for traditional I<sup>2</sup>C-bus/SMBus applications, 12.5 MHz I3C-bus applications and also higher speed SPI applications (with two devices). It features two 1-bit input-output ports (An and Bn), one output enable input (OE) and two supply pins (V<sub>CCA</sub> and V<sub>CCB</sub>). V<sub>CCA</sub> can be supplied at any voltage between 0.72 V and 1.98 V and V<sub>CCB</sub> can be supplied at any voltage between 0.72 V and 1.98 V, making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V and 1.8 V). V<sub>CCA</sub> must be  $\leq$  V<sub>CCB</sub> to ensure proper operation.

P3A9606JK can be used for both open drain as well as push-pull application which allows for level translation applications using I3C,  $I^2C$  and SPI protocols.

Pins An are referenced to V<sub>CCA</sub> and pins Bn are referenced to V<sub>CCB</sub>. The active HIGH OE pin is referenced to V<sub>CCA</sub> and controllable by a signal in either V<sub>CCA</sub> or V<sub>CCB</sub> domain. A LOW level at pin OE causes the outputs to be in a high-impedance OFF-state. This device is fully specified for partial power-down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

### 2 Features and benefits

- Wide supply voltage range:
  - V<sub>CCA</sub>: 0.72 V to 1.98 V and V<sub>CCB</sub>: 0.72 V to 1.98 V; V<sub>CCA</sub>  $\leq$  V<sub>CCB</sub>
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation
- Inputs accept voltages up to 1.98 V and are overvoltage tolerant to 1.98 V
- Provided voltage level translation for I3C, I<sup>2</sup>C-bus, SMBus and SPI devices
- ESD protection:
  - HBM JESD22-A114E Class 2 exceeds 2000 V
  - CDM JESD22-C101E exceeds 1000 V
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Available in X2SON8 package
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



## **3** Ordering information

Table 1. Ordering information								
Type number	Topside	Package						
	marking	Name	Description	Version				
P3A9606JK	Tx <sup>[1]</sup>	X2SON8	super thin small outline package, no leads; 8 terminals; 0.35 mm pitch; 1.35 mm x 1.0 mm x 0.32 mm body	SOT2015-1				

[1] "x" changes based on date code.

### 3.1 Ordering options

Table 2. Ordering options

Type number	Orderable part number	Package	Packing method	Minimum order quantity	Temperature
P3A9606JK	P3A9606JKZ	X2SON8	Reel 13" Q1/T1 *standard mark SMD with SSB <sup>[1]</sup>	20000	T <sub>amb</sub> = -40 °C to +125 °C

[1] This packing method uses a Static Shielding Bag (SSB) solution. Material should be kept in the sealed bag between uses.

## 4 Block diagram



#### **Pinning information** 5

### 5.1 Pinning



### 5.2 Pin description

Table 3. Pir	n description	
Symbol	Pin	Description
B2, B1	1, 8	B port - data input or output (referenced to $V_{CCB}$ )
GND	2	ground (0 V)
V <sub>CCA</sub>	3	supply voltage A
A2, A1	4, 5	A port - data input or output (referenced to $V_{CCA}$ )
OE	6	output enable input (active HIGH, referenced to $V_{CCA}$ ); signal can be from $V_{CCA}$ or $V_{CCB}$ domain
V <sub>CCB</sub>	7	supply voltage B

#### **Functional description** 6

### Table 4. Function table <sup>[1]</sup>

Supply voltage		Input	Input/output
V <sub>CCA</sub>	V <sub>CCB</sub>	OE <sup>[2]</sup>	
0.72 V to 1.98 V	0.72 V to 1.98 V	L	disconnected
0.72 V to 1.98 V	0.72 V to 1.98 V	Н	A1 = B1; A2 = B2
GND <sup>[3]</sup>	GND <sup>[3]</sup>	X	disconnected

H = HIGH voltage level; L = LOW voltage level; X = don't care [1]

VIL and VIH are referenced to V<sub>CCA</sub>. The OE can be controlled by an external device that is powered by either V<sub>CCA</sub> or V<sub>CCB</sub>. As V<sub>CCB</sub> is required to be [2] greater than  $V_{CCA}$ , the OE pin has been designed to withstand a voltage equal to  $V_{CCB}$  (up to 1.98 V per recommended functional voltage range). When either  $V_{CCA}$  or  $V_{CCB}$  is at GND level, the device goes into Power-down mode.

[3]

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#### **Limiting values** 7

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>CCA</sub>	supply voltage A	$V_{CCA} \le V_{CCB}$		-0.5	2.5	V
V <sub>CCB</sub>	supply voltage B	$V_{CCA} \le V_{CCB}$		-0.5	2.5	V
VI	input voltage	A port, B port and OE	[1]	-0.5	2.5	V
Vo	output voltage	Active mode	[1][2][3]	-0.5	V <sub>CCO</sub> + 0.25	V
		Power-down or 3-state mode	[1]	-0.5	2.5	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V		-50	-	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V		-50	-	mA
lo	output current	$V_{O} = 0 V$ to $V_{CCO}$	[2]	-	±50	mA
I <sub>CC</sub>	supply current	I <sub>CC(A)</sub> or I <sub>CC(B)</sub>		-	100	mA
I <sub>GND</sub>	ground current			-100	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C		-	125	mW

The minimum input and minimum output voltage ratings may be exceeded if the input and output current ratings are observed. [1]

[2] [3] V<sub>CCO</sub> is the supply voltage associated with the output.

V<sub>CCO</sub> + 0.25 V should not exceed 2.5 V.

#### **Recommended operating conditions** 8

#### Table 6. Recommended operating conditions<sup>[1]</sup>

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CCA</sub>	supply voltage A	$V_{CCA} \le V_{CCB}$	0.72	1.98	V
V <sub>CCB</sub>	supply voltage B	$V_{CCA} \le V_{CCB}$	0.72	1.98	V
VI	input voltage	A port, B port and OE	0	1.98	V
V <sub>O</sub>	output voltage	Power-down or 3-state mode; $V_{CCA}$ = 0.72 V to 1.98 V; $V_{CCB}$ = 0.72 V to 1.98 V			
		A port	0	1.98	V
		B port	0	1.98	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
TJ	junction temperature <sup>[2]</sup>		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CCA}$ = 0.72 V to 1.98 V; $V_{CCB}$ = 0.72 V to 1.98 V	-	<5.3	ns/V

[1]

The A and B sides of an unused I/O pair must be held in the same state, both at V<sub>CCI</sub> or both at GND. The T<sub>J</sub> limits shall be supported by proper thermal PCB design taking the power consumption and the thermal resistance as listed in <u>Table 7</u> into account. [2]

#### **Thermal characteristics** 9

Table 7.	Thermal	characteristics
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Symbol	Parameter	Conditions	Value (typ)	Unit
R <sub>th(j-a)</sub>	Thermal resistance from junction to ambient	X2SON8 package	114.9	°C/W
Ψ <sub>(j-t)</sub>	Junction to top characterization	X2SON8 package	1.6	°C/W

## 10 Static characteristics

#### Table 8. Typical static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T<sub>amb</sub> = 25 °C.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>OH</sub>	HIGH-level output voltage	A port; $V_{CCA}$ = 1.2 V; $I_0$ = -20 $\mu$ A		-	1.1	-	V
V <sub>OL</sub>	LOW-level output voltage	A port; V <sub>CCA</sub> = 1.2 V; I <sub>O</sub> = 20 μA		-	0.09	-	V
lı	input leakage current	OE input; V <sub>I</sub> = 0 V or 1.98 V; V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V		-	-	±1	μA
I <sub>OZ</sub>	OFF-state output current	A or B port; $V_0 = 0$ V to $V_{CCO}$ ; $V_{CCA} = 0.72$ V to 1.98 V; $V_{CCB} = 0.72$ V to 1.98 V	[1]	-	-	±1	μA
I <sub>OFF</sub>	power-off leakage current	A port; V <sub>1</sub> or V <sub>0</sub> = 0 V to 1.98 V; V <sub>CCA</sub> = 0 V; V <sub>CCB</sub> = 0 V to 1.98 V		-	-	±1	μA
		B port; V <sub>1</sub> or V <sub>0</sub> = 0 V to 1.98 V; V <sub>CCB</sub> = 0 V; V <sub>CCA</sub> = 0 V to 1.98 V		-	-	±1	μA
I <sub>CC</sub>	supply current	$V_{I} = 0 V \text{ or } V_{CCI}; I_{O} = 0 A$	[2]				
		$I_{CC(A)}$ ; $V_{CCA}$ = 0.72 V; $V_{CCB}$ = 0.72 V to 1.98 V		-	0.05	-	μA
		$I_{CC(B)}$ ; $V_{CCA}$ = 0.72 V; $V_{CCB}$ = 0.72 V to 1.98 V		-	3.3	-	μA
		$I_{CC(A)} + I_{CC(B)}$ ; $V_{CCA} = 0.72$ V; $V_{CCB} = 0.72$ V to 1.98 V		-	3.5	-	μA
CI	input capacitance	OE input; V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V		-	1.0	-	pF
C <sub>I/O</sub>	input/output	A port; $V_{CCA}$ = 0.72 V to 1.98 V; $V_{CCB}$ = 0.72 V to 1.98 V		-	4.0	-	pF
	capacitance	B port; V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V		-	4.0	-	pF

 $V_{\text{CCO}}$  is the supply voltage associated with the output.  $V_{\text{CCI}}$  is the supply voltage associated with the input. [1] [2]

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### Table 9. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).<sup>[1]</sup>

Symbol	Parameter	Conditions		-40 °C to	o +85 °C	-40 °C to	+125 °C	Unit
				Min	Max	Min	Max	
V <sub>IH</sub>	HIGH-level	A port or B port						
	input voltage	V <sub>CCA</sub> = 0.72 V to 0.9 V; V <sub>CCB</sub> = 0.72 V to 0.9 V	[1]	V <sub>CCI</sub> - 0.2	-	V <sub>CCI</sub> - 0.2	-	V
	V <sub>CCA</sub> = 0.9 V to 1.98 V; V <sub>CCB</sub> = 0.9 V to 1.98 V	[1]	V <sub>CCI</sub> - 0.4	-	V <sub>CCI</sub> - 0.4	-	V	
		OE input						
		V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V		0.65V <sub>CCA</sub>	-	0.65V <sub>CCA</sub>	-	V
V <sub>IL</sub>	LOW-level	A or B port						
	input voltage	$V_{CCA} = 0.72 V \text{ to } 1.98 V; V_{CCB} = 0.72 V \text{ to } 1.98 V$		-	0.3V <sub>CCA</sub>	-	0.3V <sub>CCA</sub>	V
		OE input						
		V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V		-	0.3V <sub>CCA</sub>	-	0.3V <sub>CCA</sub>	V
V <sub>OH</sub>	HIGH-level	I <sub>O</sub> = -20 μA	[2]					
	output voltage	A port; V <sub>CCA</sub> = 0.72 V to 1.98 V		V <sub>CCO</sub> - 0.4	-	V <sub>CCO</sub> - 0.4	-	V
		B port; V <sub>CCB</sub> = 0.72 V to 1.98 V		V <sub>CCO</sub> - 0.4	-	V <sub>CCO</sub> - 0.4	-	V
V <sub>OL</sub>	LOW-level	I <sub>O</sub> = 20 μA	[2]					
	output voltage	A port; V <sub>CCA</sub> = 0.72 V to 1.98 V		-	0.3	-	0.3	V
		B port; V <sub>CCB</sub> = 0.72 V to 1.98 V		-	0.3	-	0.3	V
lı	input leakage current	OE input; V <sub>I</sub> = 0 V to 1.98 V; V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V		-	±2	-	±5	μA
I <sub>OZ</sub>	OFF-state output current	A or B port; $V_0 = 0 V$ or $V_{CCO}$ ; $V_{CCA} = 0.72 V$ to 1.98 V; $V_{CCB} = 0.72 V$ to 1.98 V	[2]	-	±2	-	±10	μA
I <sub>OFF</sub>	power-off leakage	A port; V <sub>1</sub> or V <sub>0</sub> = 0 V to 1.98 V; V <sub>CCA</sub> = 0 V; V <sub>CCB</sub> = 0 V to 1.98 V		-	±2	-	±10	μA
	current	B port; $V_1$ or $V_0$ = 0 V to 1.98 V; $V_{CCB}$ = 0 V; $V_{CCA}$ = 0 V to 1.98 V		-	±2	-	±10	μA
I <sub>CC</sub>	supply current	$V_{I} = 0 V \text{ or } V_{CCI}; I_{O} = 0 A$	[1]					
		I <sub>CC(A)</sub>						
		OE = LOW; V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V		-	5	-	15	μA

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### Table 9. Static characteristics...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).<sup>[1]</sup>

Symbol	Parameter	Conditions	-40 °C 1	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Мах	Min	Мах	
		OE = HIGH; V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V	-	6	-	20	μA
		V <sub>CCA</sub> = 1.98 V; V <sub>CCB</sub> = 0 V	-	3.5	-	15	μA
		V <sub>CCA</sub> = 0 V; V <sub>CCB</sub> = 1.98 V	-	-2	-	-15	μA
		I <sub>CC(B)</sub>					
		OE = LOW; V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V	-	8	-	29	μA
		OE = HIGH; V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V	-	11	-	36	μA
		V <sub>CCA</sub> = 1.98 V; V <sub>CCB</sub> = 0 V	-	-2	-	-15	μA
		V <sub>CCA</sub> = 0 V; V <sub>CCB</sub> = 1.98 V	-	6	-	20	μA
		$I_{CC(A)} + I_{CC(B)}$					
		OE = LOW; V <sub>CCA</sub> = 0.72 V to 1.98 V; V <sub>CCB</sub> = 0.72 V to 1.98 V	-	16	-	56	μA

[1]

 $V_{\text{CCI}}$  is the supply voltage associated with the input.  $V_{\text{CCO}}$  is the supply voltage associated with the output. [2]

### **11** Dynamic characteristics

### Table 10. Dynamic characteristics for temperature range -40 °C to +85 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Symbol	Parameter	Conditions		V <sub>CCB</sub>			V <sub>CCB</sub>		Unit
			1.2 V ± 10 %				1.8 V ± 10 %		
			Min	Тур	Мах	Min	Тур	Мах	
<b>V<sub>CCA</sub> = 0.8</b>	V <b>±</b> 10 %								
t <sub>pd</sub>	propagation delay	A to B; C <sub>L</sub> = 15 pF	2.1	5.6	7.7	1.7	3.9	5.3	ns
		B to A; C <sub>L</sub> = 15 pF	1.2	10.6	19.9	0.5	9.6	17.2	ns
t <sub>en</sub>	enable time	OE to A, B; C <sub>L</sub> = 15 pF	16	125	150	16	120	160	ns
t <sub>dis</sub> <sup>[2]</sup>	disable time	OE to A; no external load <sup>[3]</sup>	10		25	10		25	ns
		OE to B; no external load <sup>[3]</sup>	10		25	10		25	ns
		OE to A; C <sub>L</sub> = 15 pF			50			50	ns
		OE to B; C <sub>L</sub> = 15 pF			50			50	ns
t <sub>t</sub>	transition time	A port; C <sub>L</sub> = 15 pF	2.1	8.5	17.5	1.5	9	15.4	ns
		B port; C <sub>L</sub> = 15 pF	1.1	4	5.8	0.7	1.5	2.1	ns
t <sub>sk(o)</sub>	output skew time	delta between channels [4]	0	0.2	0.4	0	0.2	0.4	ns
tw	pulse width	data inputs	37			37			ns
f <sub>data</sub>	data rate		0.064		26	0.064		26	Mbps

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{en}$  is the same as  $t_{PZH}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_i$  is the same as  $t_{THL}$  and  $t_{TLH}$ .

[2] Guaranteed by design.

[3] Delay between OE going LOW and when the outputs are actually disabled.

[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

Table 11.	<b>Dynamic characteristics</b>	for temperature range	-40 °C to +85 °C <sup>[1]</sup>
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Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Symbol	Parameter	Conditions		V <sub>CCB</sub>			V <sub>CCB</sub>		Unit
				1.2 V ± 1	0 %		1.8 V ± 10 %		
			Min	Тур	Мах	Min	Тур	Мах	
<b>V<sub>CCA</sub> =</b> 1.2	V ± 10 %				1				,
t <sub>pd</sub>	propagation delay	A to B; C <sub>L</sub> = 15 pF	1.5	4.5	6.1	1.0	2.5	3.5	ns
		B to A; C <sub>L</sub> = 15 pF	1.1	3.9	5.3	0.6	2.8	3.9	ns
t <sub>pdc</sub>	propagation delay	A to B; C <sub>L</sub> = 80 pF	NA	NA	NA	2.5	4.9	7	ns
		B to A; C <sub>L</sub> = 30 pF	NA	NA	NA	0.9	3.4	5	ns
t <sub>en</sub>	enable time	OE to A, B; C <sub>L</sub> = 15 pF	10	50	100	10	50	100	ns
t <sub>dis</sub> <sup>[2]</sup> disa	disable time	OE to A; no external load <sup>[3]</sup>	10		25	10		25	ns
		OE to B; no external load <sup>[3]</sup>	10		25	10		25	ns
		OE to A; C <sub>L</sub> = 15 pF			50	-		50	ns
		OE to B; $C_L = 15 \text{ pF}$			50	-		50	ns
t <sub>t</sub>	transition time	A port; C <sub>L</sub> = 15 pF	0.8	2.6	3.5	0.6	1.5	2.5	ns
		B port; C <sub>L</sub> = 15 pF	1.1	3.6	5.1	0.6	1.3	2.2	ns
t <sub>tc</sub>	transition time	A port; C <sub>L</sub> = 30 pF	NA	NA	NA	1.0	2.2	3.6	ns
		B port; C <sub>L</sub> = 80 pF	NA	NA	NA	2.5	4.3	6.3	ns
t <sub>sk(o)</sub>	output skew time	delta between channels <sup>[4]</sup>	0.0	0.1	0.2	0.0	0.1	0.3	ns
t <sub>W</sub>	pulse width	data inputs	15			13.5			ns
f <sub>data</sub>	data rate		0.064		52	0.064		52	Mbps

 $[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{en} is the same as t_{PZL} and t_{PZH}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_i is the same as t_{THL} and t_{TLH}.$ 

[2] Guaranteed by design.

[3] Delay between OE going LOW and when the outputs are actually disabled.

[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

#### Table 12. Dynamic characteristics for temperature range -40 °C to +85 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol	Parameter	Conditions		V <sub>CCB</sub>		Unit
				1.8 V ± 1	0 %	
			Min	Тур	Мах	
V <sub>CCA</sub> = 1.8 V ±	10 %		'		,	
t <sub>pd</sub>	propagation delay	A to B; C <sub>L</sub> = 15 pF	1	2.5	3.4	ns
		B to A; C <sub>L</sub> = 15 pF	0.7	2.3	3	ns
t <sub>en</sub>	enable time	OE to A, B; $C_L$ = 15 pF	8	25	50	ns
<sup>[2]</sup> disable time	disable time	OE to A; no external load <sup>[3]</sup>	10		25	ns
		OE to B; no external load <sup>[3]</sup>	10		25	ns
		OE to A; C <sub>L</sub> = 15 pF			50	ns
		OE to B; C <sub>L</sub> = 15 pF			50	ns
t <sub>t</sub>	transition time	A port; C <sub>L</sub> = 15 pF	0.5	1.2	1.7	ns
		B port; C <sub>L</sub> = 15 pF	0.7	1.7	2.5	ns
t <sub>sk(o)</sub>	output skew time	delta between channels <sup>[4]</sup>	0	0.1	0.2	ns
Ŵ	pulse width	data inputs	13.5			ns
f <sub>data</sub>	data rate		0.064		52	Mbps

[1] t<sub>pd</sub> is the same as t<sub>PLL</sub> and t<sub>PHL</sub>; t<sub>en</sub> is the same as t<sub>PZL</sub> and t<sub>PZL</sub>; t<sub>dis</sub> is the same as t<sub>PLZ</sub> and t<sub>PHZ</sub>; t<sub>t</sub> is the same as t<sub>THL</sub> and t<sub>TLH</sub>.

[2] Ġuaranteed by design.

[3] Delay between OE going LOW and when the outputs are actually disabled.

[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

Table 13. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Symbol Parameter		Conditions	V <sub>CCB</sub>	V <sub>CCB</sub> 1.2 V ± 10 %			V <sub>CCB</sub> 1.8 V ± 10 %		Unit
			1.2 V ± 10						
			Min	Тур	Max	Min	Тур	Мах	
<b>V<sub>CCA</sub> = 0.8</b>	V <b>±</b> 10 %			ł					
t <sub>pd</sub>	propagation delay	A to B; C <sub>L</sub> = 15 pF	2.1	5.6	7.7	1.7	3.9	5.3	ns

### Table 13. Dynamic characteristics for temperature range -40 °C to +125 °C <sup>[1]</sup>...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Symbol	Parameter	Conditions	V <sub>CCB</sub>			V <sub>CCB</sub>			Unit	
			1.2 V ± 10 %			1.8 V ± 10				
			Min	Тур	Мах	Min	Тур	Мах		
		B to A; C <sub>L</sub> = 15 pF	1.2	10.6	19.9	0.5	9.6	17.2	ns	
t <sub>en</sub>	enable time	OE to A, B; C <sub>L</sub> = 15 pF	16	125	150	16	120	160	ns	
t <sub>dis</sub> <sup>[2]</sup>	disable time	OE to A; no external load <sup>[3]</sup>	10		25	10		25	ns	
		OE to B; no external load <sup>[3]</sup>	10		25	10		25	ns	
		OE to A; $C_L = 15 \text{ pF}$			50			50	ns	
		OE to B; $C_L = 15 \text{ pF}$			50			50	ns	
t <sub>t</sub>	transition time	A port; C <sub>L</sub> = 15 pF	2.1	8.5	17.5	1.5	9	15.4	ns	
		B port; C <sub>L</sub> = 15 pF	1.1	4	5.8	0.7	1.5	2.1	ns	
t <sub>sk(o)</sub>	output skew time	delta between channels <sup>[4]</sup>	0	0.2	0.4	0	0.2	0.4	ns	
t <sub>W</sub>	pulse width	data inputs	37			37			ns	
f <sub>data</sub>	data rate		0.064		26	0.064		26	Mbps	

[1]  $t_{pd}$  is the same as  $t_{PLL}$  and  $t_{PHL}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZL}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .

[2] Ġuaranteed by design.

[3] Delay between OE going LOW and when the outputs are actually disabled.

[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

#### Table 14. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol Parameter	Parameter	Conditions	V <sub>CCB</sub>				V <sub>CCB</sub> 1.8 V ± 10 %		
			1.2 V ± 1						
			Min	Тур	Мах	Min	Тур	Max	
<b>V<sub>CCA</sub></b> = 1.2 V ±	10 %		i .						,
t <sub>pd</sub>	propagation delay	A to B; C <sub>L</sub> = 15 pF	1.5	4.5	6.2	1.0	2.5	3.6	ns
		B to A; C <sub>L</sub> = 15 pF	1.1	3.9	5.4	0.6	2.8	4.0	ns
t <sub>pdc</sub>	propagation delay	A to B; C <sub>L</sub> = 80 pF	NA	NA	NA	2.5	4.9	7.4	ns

Symbol	Parameter	Conditions	V <sub>CCB</sub>			V <sub>CCB</sub>			Unit
			1.2 V ± 1	1.2 V ± 10 %			1.8 V ± 10 %		
			Min	Тур	Мах	Min	Тур	Мах	
		B to A; C <sub>L</sub> = 30 pF	NA	NA	NA	0.9	3.4	5.3	ns
en	enable time	OE to A, B; $C_L$ = 15 pF	10	50	100	10	50	100	ns
[2] dis	disable time	OE to A; no external load <sup>[3]</sup>	10		25	10		25	ns
		OE to B; no external load <sup>[3]</sup>	10		25	10		25	ns
		OE to A; $C_L$ = 15 pF			50	-		50	ns
		OE to B; $C_L$ = 15 pF			50	-		50	ns
	transition time	A port; C <sub>L</sub> = 15 pF	0.8	2.6	3.5	0.6	1.5	2.6	ns
		B port; C <sub>L</sub> = 15 pF	1.1	3.6	5.1	0.6	1.3	2.3	ns
tc	transition time	A port; C <sub>L</sub> = 30 pF	NA	NA	NA	1.0	2.2	3.8	ns
		B port; C <sub>L</sub> = 80 pF	NA	NA	NA	2.5	4.3	6.9	ns
sk(o)	output skew time	delta between channels <sup>[4]</sup>	0	0.1	0.2	0	0.1	0.3	ns
N	pulse width	data inputs	15			13.5			ns
data	data rate		0.064		52	0.064		52	Mbps

Table 14. Dynamic characteristics for temperature range -40 °C to +125 °C <sup>[1]</sup>...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZL}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .

[2] Ġuaranteed by design.

[3] Delay between OE going LOW and when the outputs are actually disabled.

[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

#### Table 15. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol	Parameter	Conditions		V <sub>CCB</sub>		
			1.8 V ± 10 %			
			Min	Тур	Мах	
<b>V<sub>CCA</sub></b> = 1.8 ∨ ± 10 %	6		,			
t <sub>pd</sub>	propagation delay	A to B; C <sub>L</sub> = 15 pF	1	2.5	3.5	ns

#### Table 15. Dynamic characteristics for temperature range -40 °C to +125 °C <sup>[1]</sup>...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol	Parameter	Conditions		V <sub>CCE</sub>	3	Unit
					0 %	
			Min	Тур	Мах	
		B to A; C <sub>L</sub> = 15 pF	0.7	2.3	3.1	ns
en	enable time	OE to A, B; $C_L = 15 \text{ pF}$	8	25	50	ns
t <sub>dis</sub> <sup>[2]</sup>	disable time	OE to A; no external load <sup>[3]</sup>	10		25	ns
		OE to B; no external load <sup>[3]</sup>	10		25	ns
		OE to A; C <sub>L</sub> = 15 pF			50	ns
		OE to B; C <sub>L</sub> = 15 pF			50	ns
t	transition time	A port; C <sub>L</sub> = 15 pF	0.5	1.2	1.7	ns
		B port; C <sub>L</sub> = 15 pF	0.7	1.7	2.6	ns
t <sub>sk(o)</sub>	output skew time	delta between channels <sup>[4]</sup>	0	0.1	0.2	ns
tw	pulse width	data inputs	13.5			ns
f <sub>data</sub>	data rate		0.064		52	Mbps

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{pZH}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{pHZ}$ ;  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .

[2] Guaranteed by design.

[3] Delay between OE going LOW and when the outputs are actually disabled.

[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

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## 12 Waveforms



#### Table 16. Measurement points

 $V_{CCI}$  is the supply voltage associated with the input and  $V_{CCO}$  is the supply voltage associated with the output.

Supply voltage	Input	Output		
V <sub>cco</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
0.8 V ± 10 %	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.08 V	V <sub>OH</sub> - 0.08 V
1.2 V ± 10 %	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.12 V	V <sub>OH</sub> - 0.12 V
1.8 V ± 10 %	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.18 V	V <sub>OH</sub> - 0.18 V

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Figure 4. Test circuit for measuring switching times

Supply voltage		Input		Load		V <sub>EXT</sub>		
V <sub>CCA</sub>	V <sub>CCB</sub>	V <sub>I</sub> <sup>[1]</sup>	Δt/ΔV	CL	R <sub>L</sub> <sup>[2]</sup>	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	$t_{PZL}, t_{PLZ}$ <sup>[3]</sup>
0.72 V to 1.98 V	0.72 V to 1.98 V	V <sub>CCI</sub>	≤ 1.0 ns/V	15 pF	50 kΩ, 1 MΩ	open	open	2V <sub>CCO</sub>

[1] V<sub>CCI</sub> is the supply voltage associated with the input.

[2] For measuring data rate, pulse width, propagation delay and output rise and fall measurements,  $R_L = 1 M\Omega$ ; for measuring enable and disable times,  $R_L = 50 k\Omega$ .

## **13** Application information

## 13.1 Applications

Voltage level-translation applications. The P3A9606JK can be used to interface between devices or systems operating at different supply voltages. See <u>Figure 5</u>, <u>Figure 6</u>, <u>Figure 7</u> and <u>Figure 8</u> for a typical operating circuit using the P3A9606JK.





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Figure 7. SPI application block diagram

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### 13.2 Architecture

The architecture uses edge-rate accelerator circuitry (for both the high-to-low and lowto-high), N-Channel Pass gate transistor and a pull-up resistor (to provide DC-bias and drive capabilities) to meet these requirements. The design is directionless and does not need direction control signal. The implementation supports both low speed Open-drain operation as well as high speed push-pull operation. The N-Channel Pass device will be on only during Low input cycle and will be off during High input cycle.

### 13.3 Input driver requirements

The continuous DC- current sinking or sourcing capability is determined by the external system-level; open-drain or push-pull drivers that are interfaced to the P3A9606JK IO pins.

The high bandwidth of these IO circuits used to facilitate this fast change from an input to an output and an output to an input, they have a modest sourcing capability of hundreds of micro-amperes, as determined by the pull-up resistor.

The fall time of a signal depends on the edge-rate and output impedance of the external driving the P3A9606JK data IOs, as well as the capacitive loading at the data lines.

### 13.4 Power-up and power-down

During operation, ensure that  $V_{CCA} \le V_{CCB}$  at all times. The sequencing of each power supply will not damage the device during the power up operation, so either power supply can be ramped up first. There is no special power-up sequencing required. The

P3A9606JK includes circuitry that disables all output ports and puts the device into a power-down mode when either  $V_{CCA}$  or  $V_{CCB}$  is switched off.

### 13.5 Enable and disable

An output enable input (OE) is used to disable the device. Setting OE = LOW causes all I/Os to assume the high-impedance OFF-state. The disable time ( $t_{dis}$  with no external load) indicates the delay between when OE goes LOW and when outputs actually become disabled. The enable time ( $t_{en}$ ) indicates the amount of time the user must allow for one one-shot circuitry to become operational after OE is taken HIGH. To ensure the high-impedance OFF-state during power-up or power-down, pin OE should be tied to GND, OE pin should not be left floating in any condition.

OE V<sub>IL</sub> and V<sub>IH</sub> are referenced to V<sub>CCA</sub>. The OE can be controlled by an external device that is powered by either V<sub>CCA</sub> or V<sub>CCB</sub>. As V<sub>CCB</sub> is required to be greater than V<sub>CCA</sub>, the OE pin has been designed to withstand a voltage equal to V<sub>CCB</sub> (up to 1.98 V per recommended functional voltage range).

### 13.6 Layout guidelines

To ensure reliability of the device, the following common printed-circuit board layout guidelines are recommended:

- Bypass capacitors should be used on power supplies and should be placed as close as possible to  $V_{CCA}$ ,  $V_{CCB}$ , and GND pins.
- · Short trace lengths should be used to avoid excessive loading.
- PCB signal trace-lengths must be kept short enough so that the round-trip delay of any reflection is less than the one-shot duration, approximately 8 ns, ensuring that any reflection encounters low impedance at the source driver.



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## 14 Package outline



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## **15 Soldering**



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2. DIMENSIONING AND TOLE	RANCING PER ASME Y14.5	M—1994.		
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## **16 Abbreviations**

Table 18. Abbreviations		
Acronym	Description	
CDM	Charged Device Model	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
НВМ	Human Body Model	
ММ	Machine Model	
NMOS	N-type Metal Oxide Semiconductor	
PMOS	P-type Metal Oxide Semiconductor	
PRR	Pulse Repetition Rate	

## 17 Revision history

### Table 19. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
P3A9606JK v.1.0	20210510	Product data sheet	-	-

## 18 Legal information

### 18.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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